

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. P27154	Application No. <b>10/708,430</b>		
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use several sheets if necessary)				Applicant Michael P. Belyansky et al.			
				Filing Date March 3, 2004		Group 2818	
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AH		JP 64-76755	3-22-1989	Japan			X
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EXAMINER /Andy Huynh/ (05/26/2006)				DATE CONSIDERED			
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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